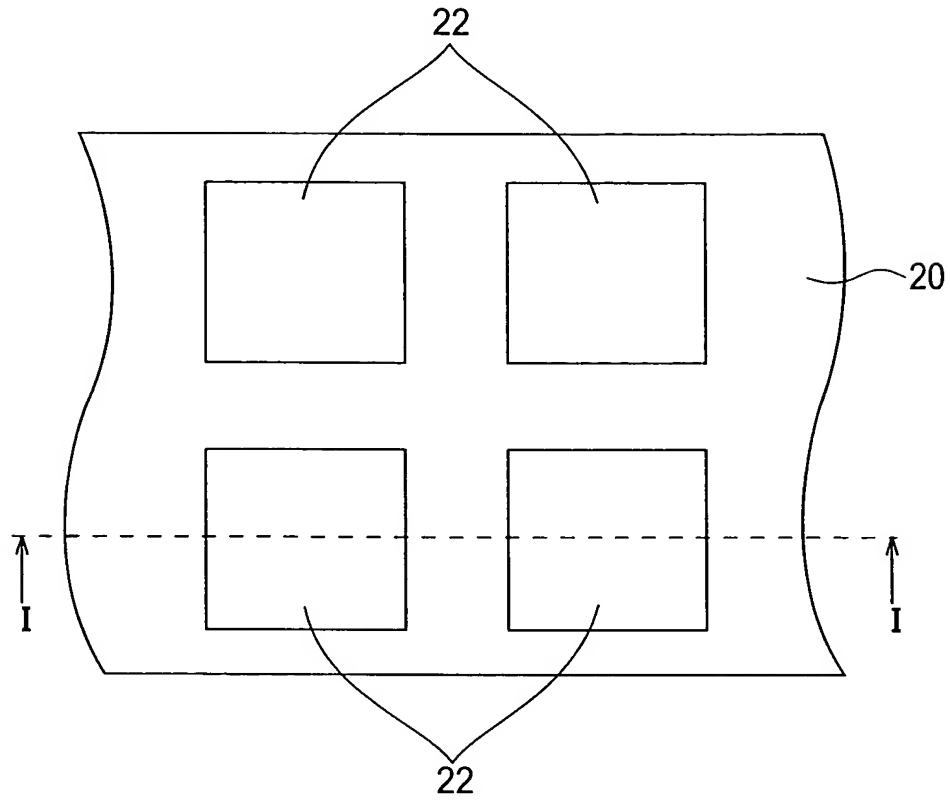


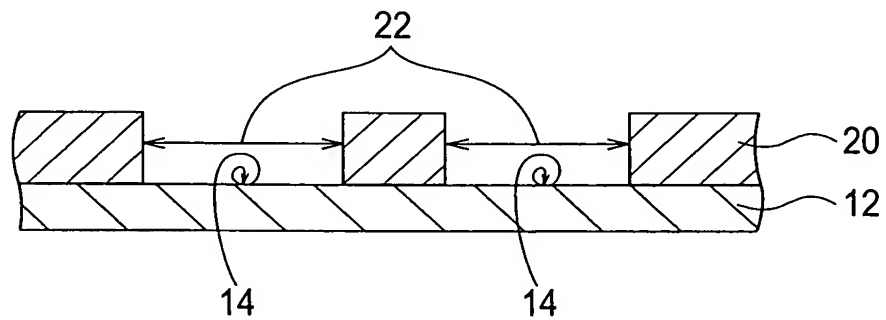




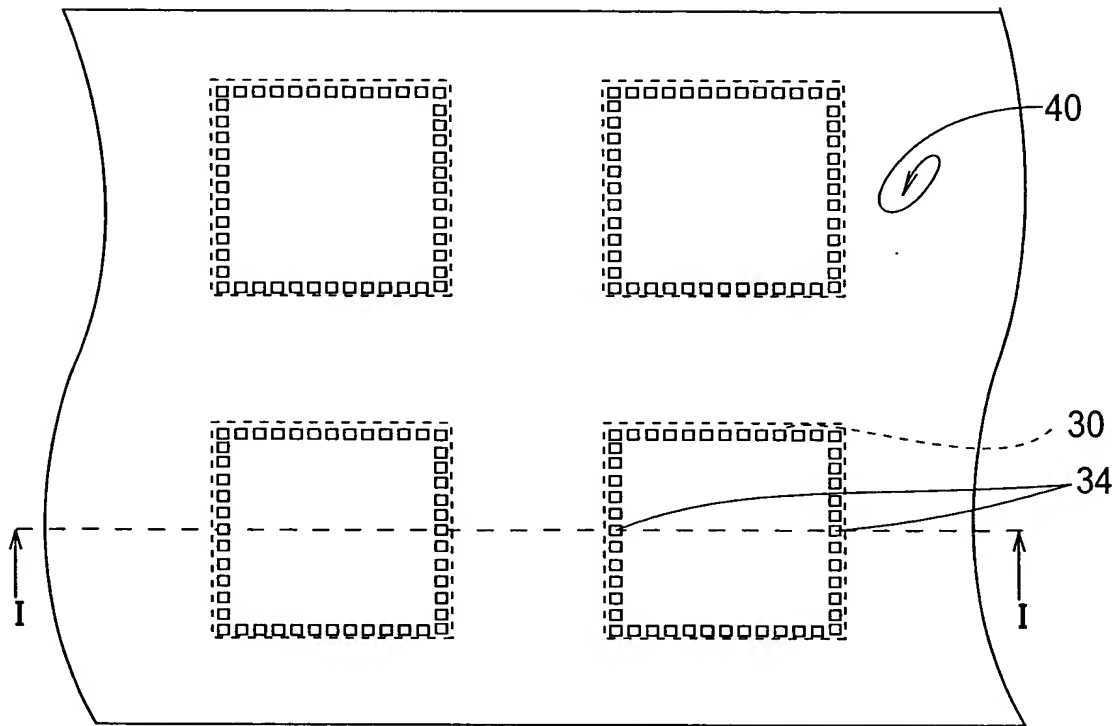
*FIG. 4(A)*



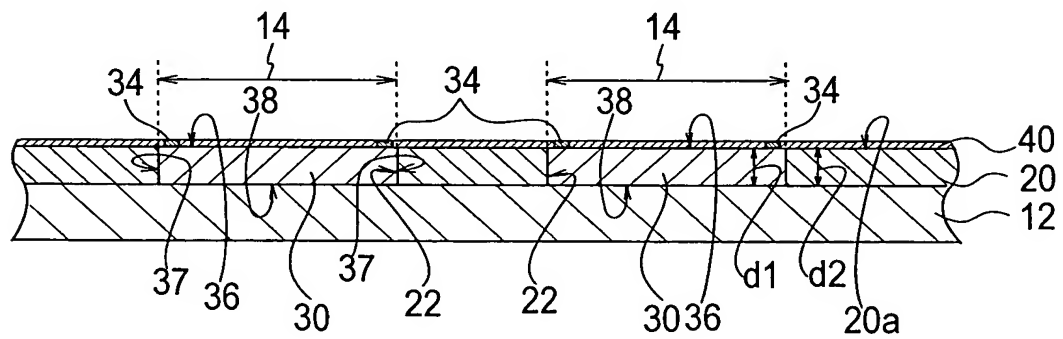
*FIG. 4(B)*



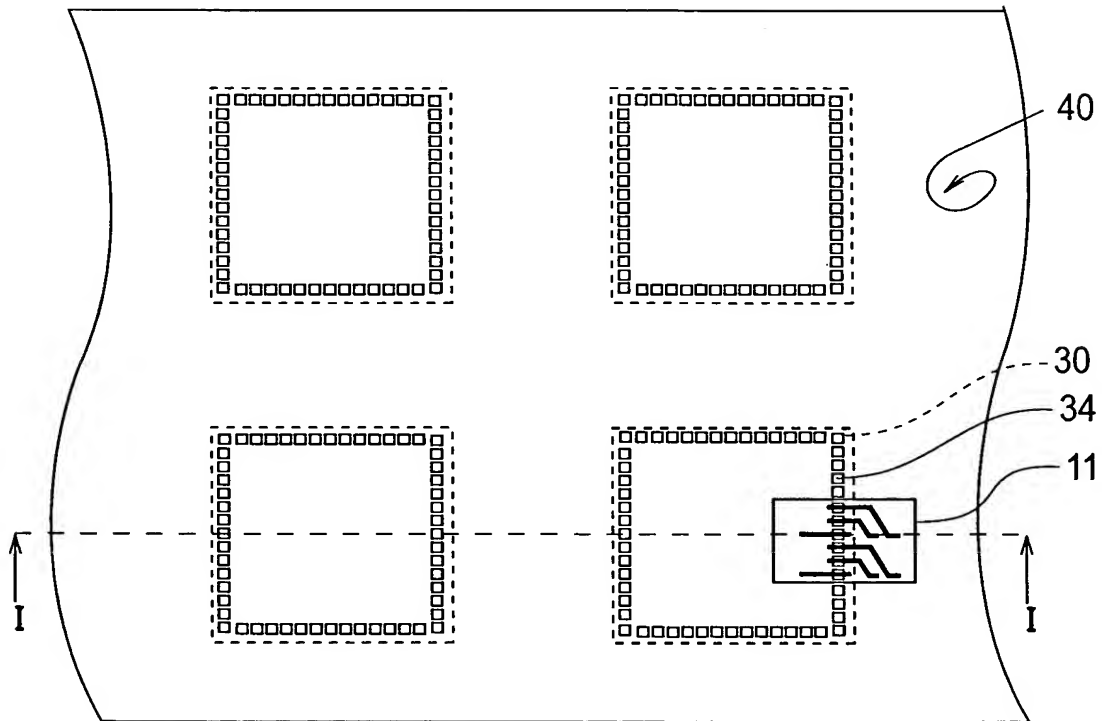
*FIG. 5(A)*



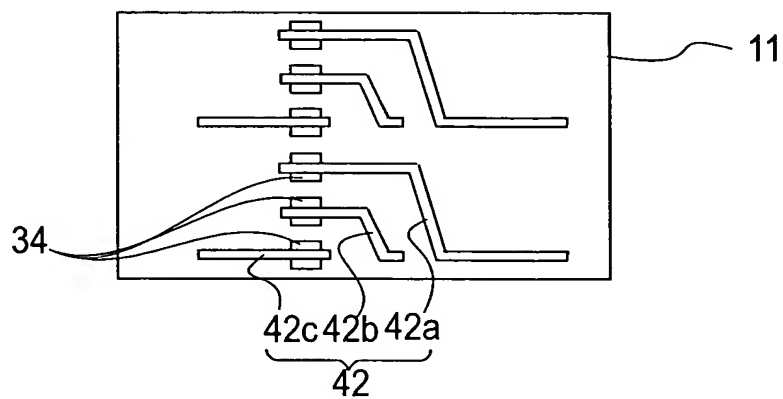
*FIG. 5(B)*



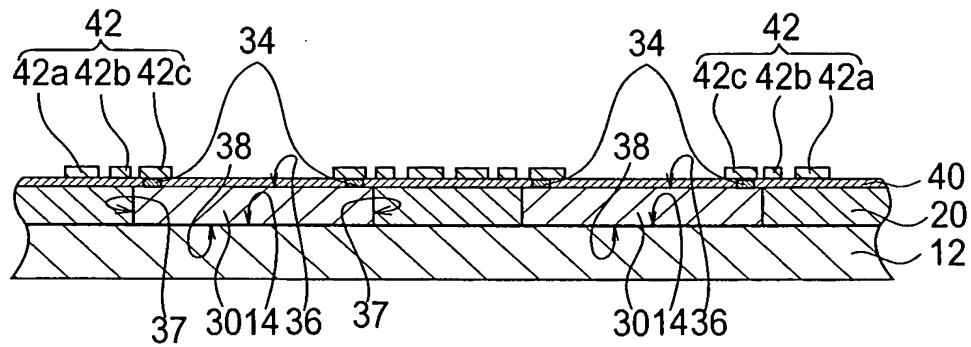
*FIG. 6(A)*

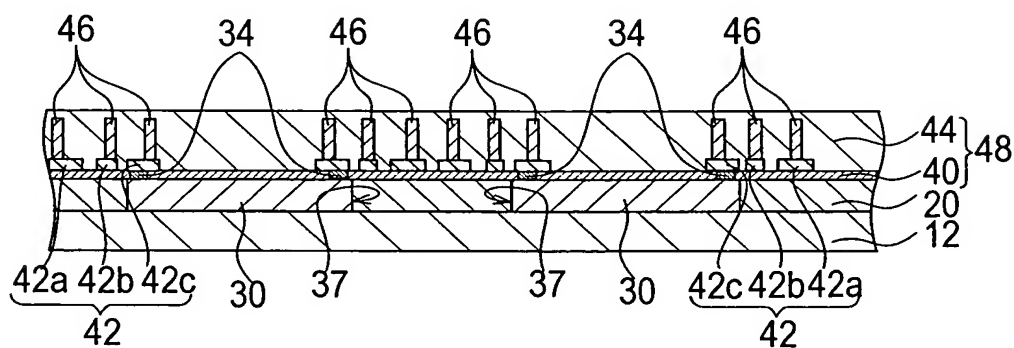


*FIG. 6(B)*



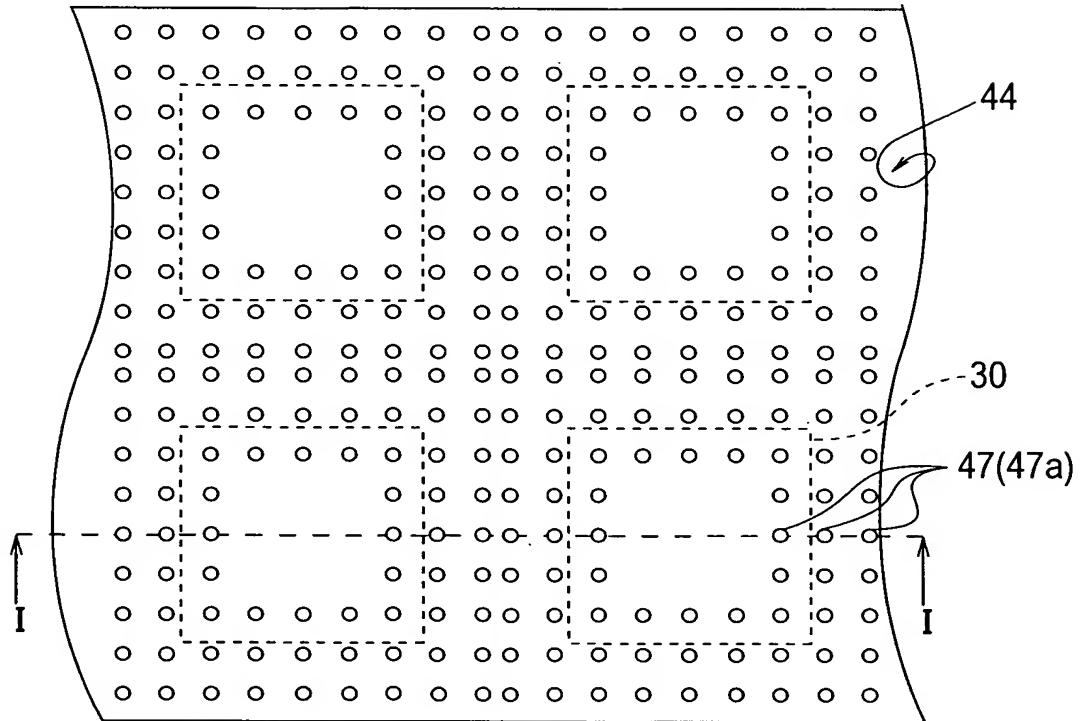
*FIG. 7*



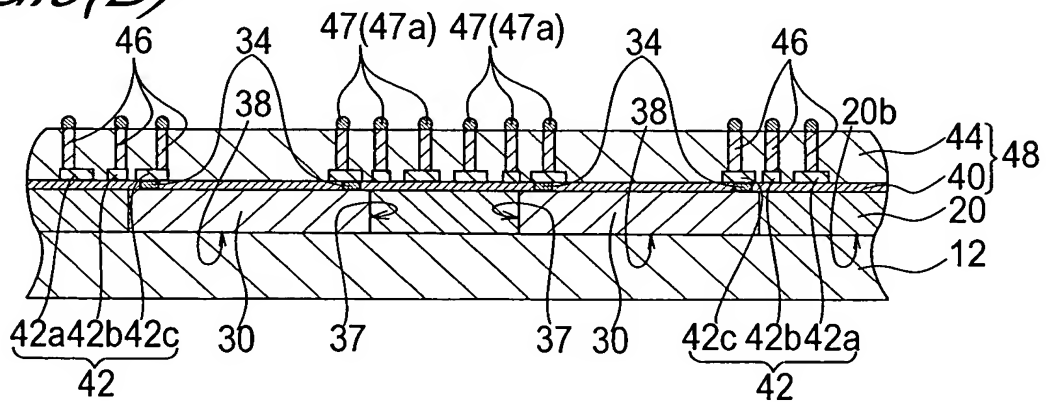




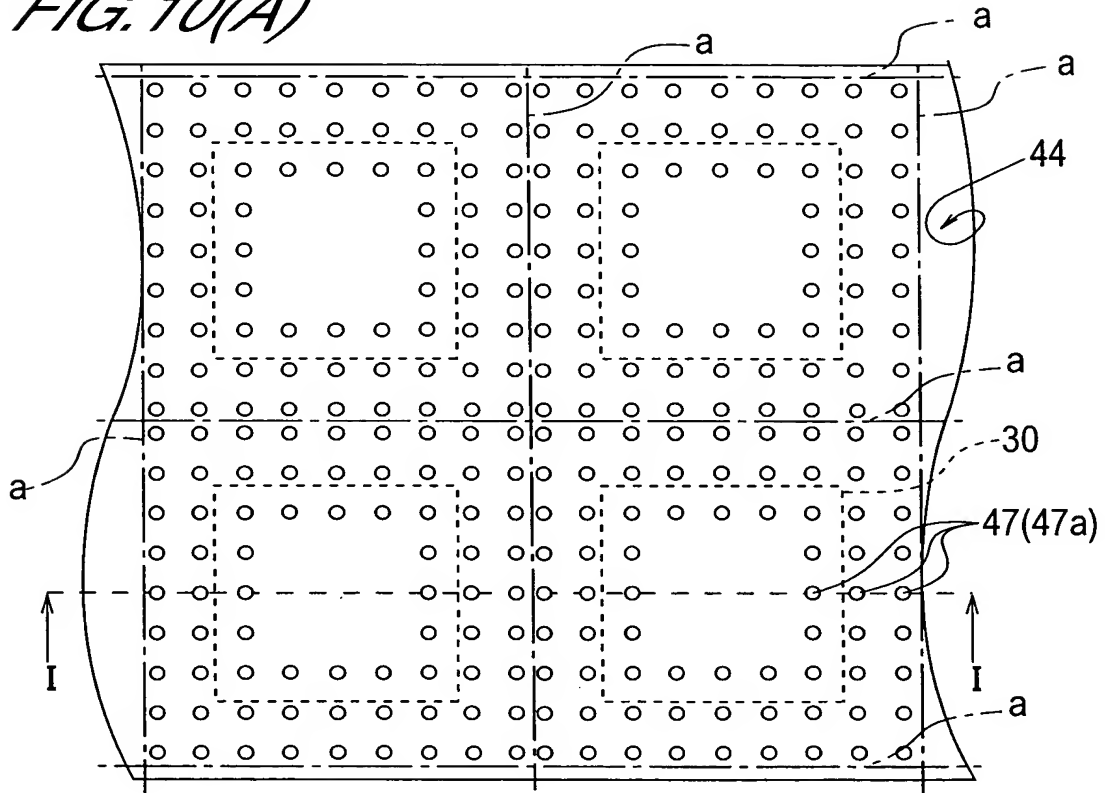
*FIG. 9(A)*



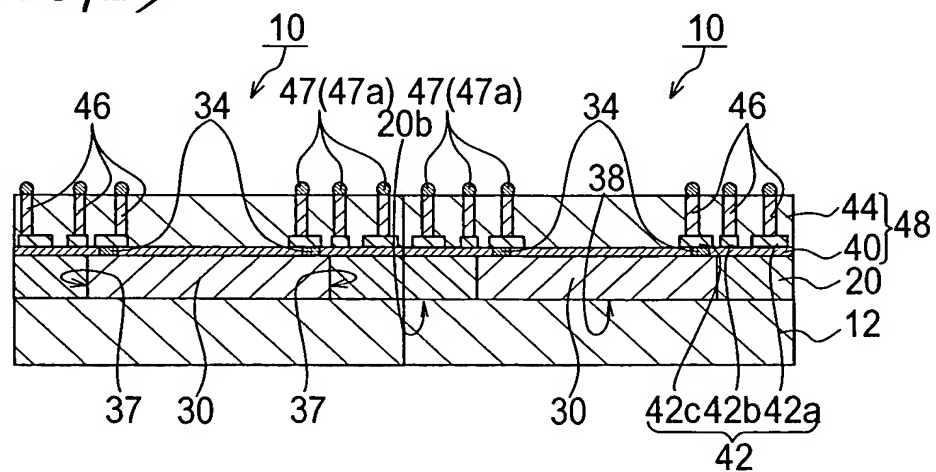
*FIG. 9(B)*



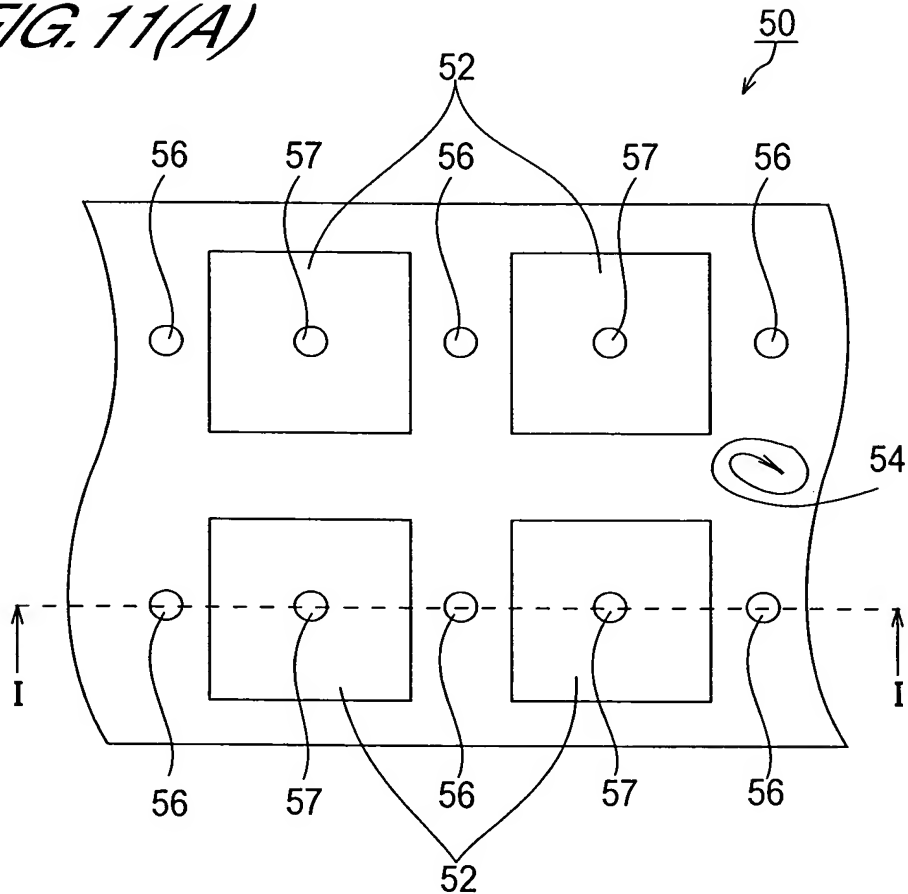
*FIG. 10(A)*



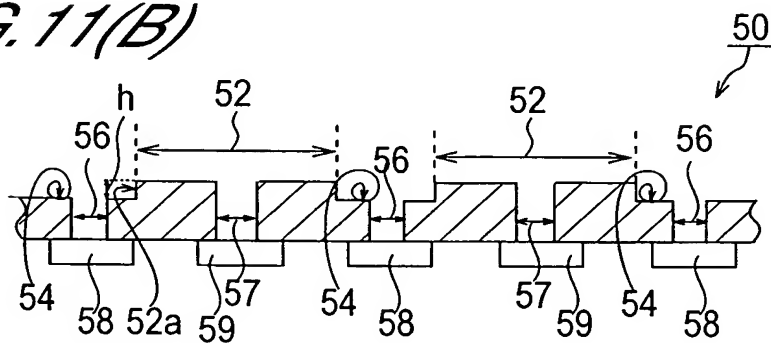
*FIG. 10(B)*



*FIG. 11(A)*

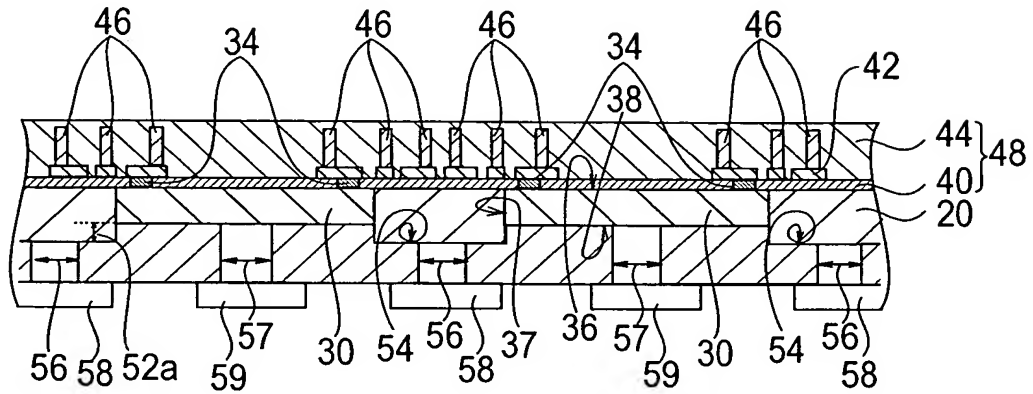


*FIG. 11(B)*

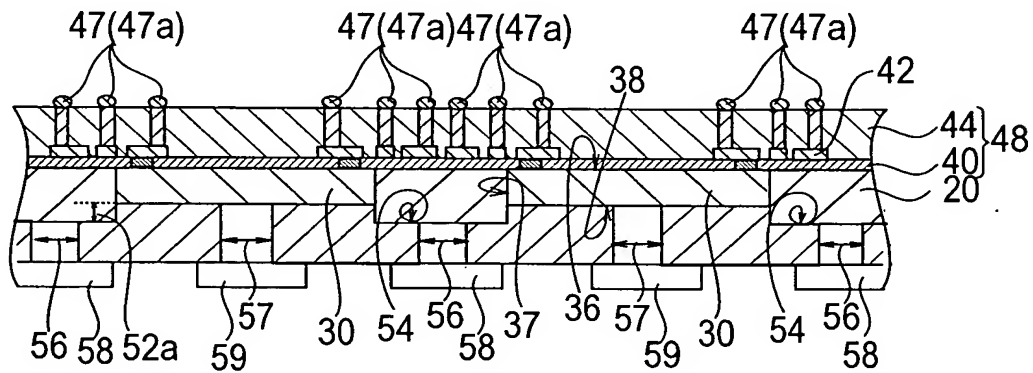


A detailed cross-sectional diagram of a semiconductor device. The device consists of a substrate 20 with a top layer 40. On the surface of the top layer 40, there are three groups of small rectangular features labeled 42. Between these groups are larger, rounded structures labeled 34. A horizontal line labeled 'h' indicates a specific height or interface. Below the top layer 40, there are several layers and regions. Regions 36 and 37 are shown as curved areas. Regions 38 and 39 are indicated by arrows pointing to specific internal structures. Various other components are labeled with numbers: 56, 58, 52a, 59, 57, 54, 30, 58, 59, 30, 54, 56, 58. Some of these labels appear to be repeated or misaligned in the original image.

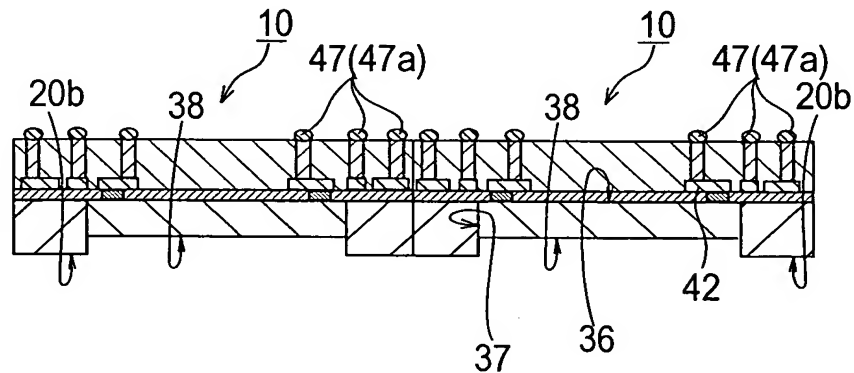
*FIG. 13(A)*



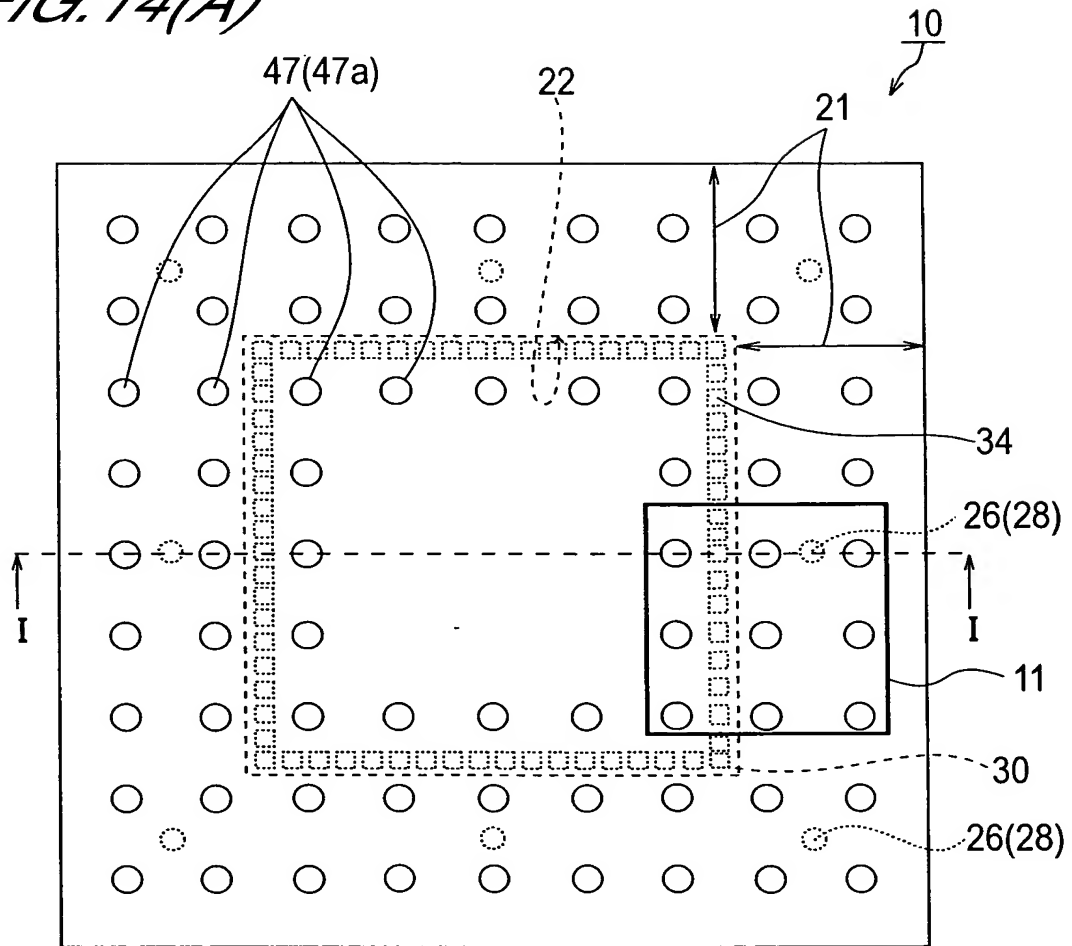
*FIG. 13(B)*



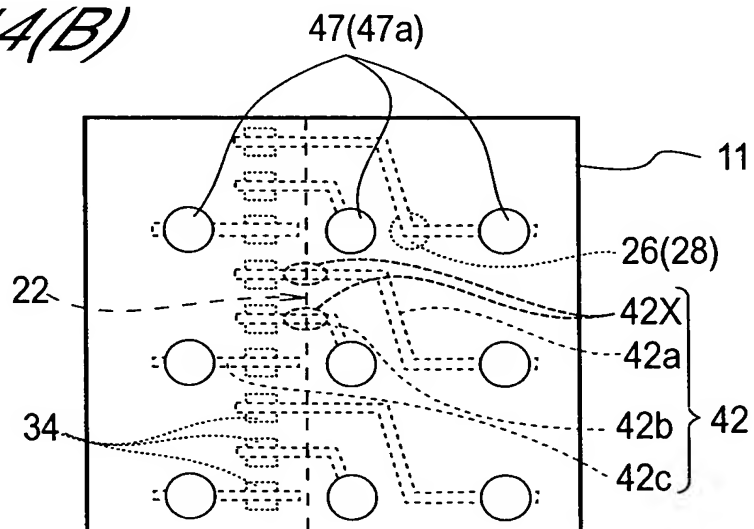
*FIG. 13(C)*



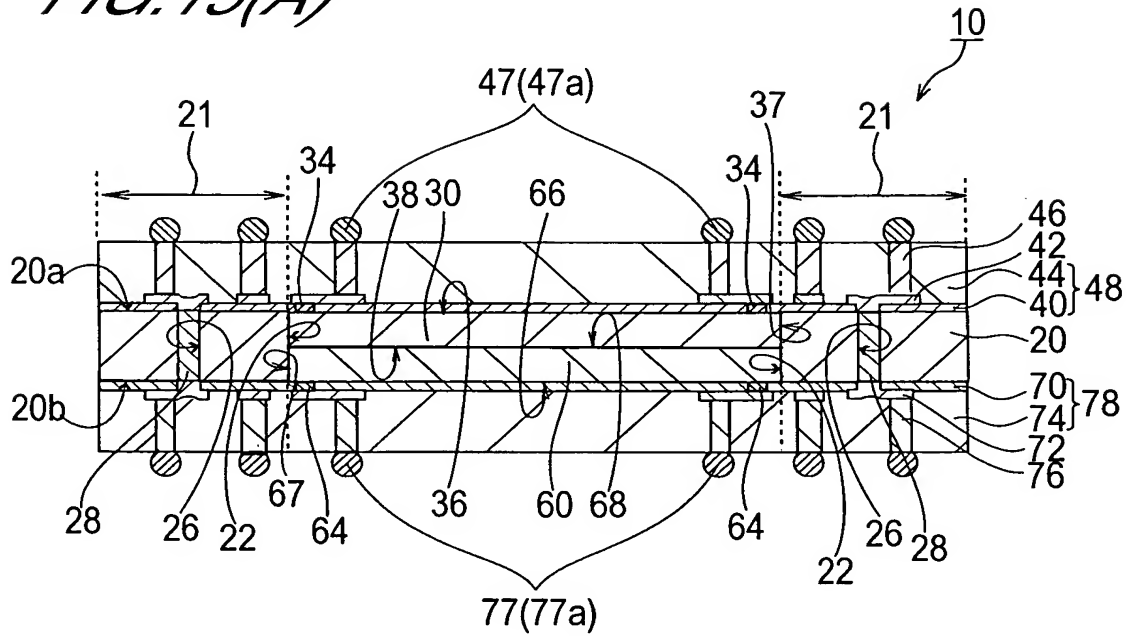
*FIG. 14(A)*



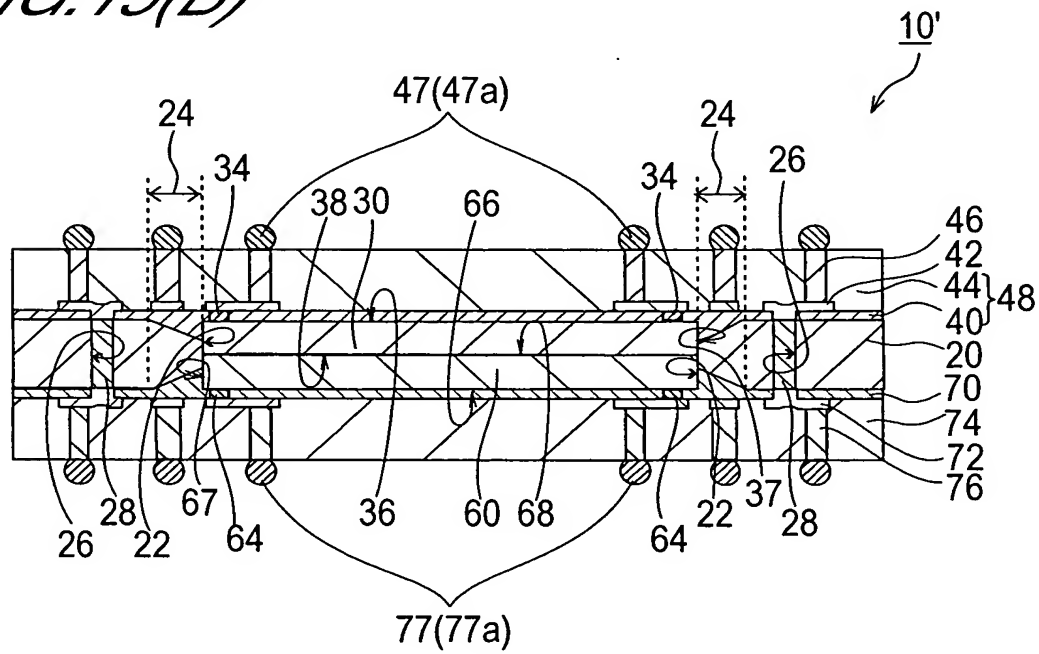
*FIG. 14(B)*



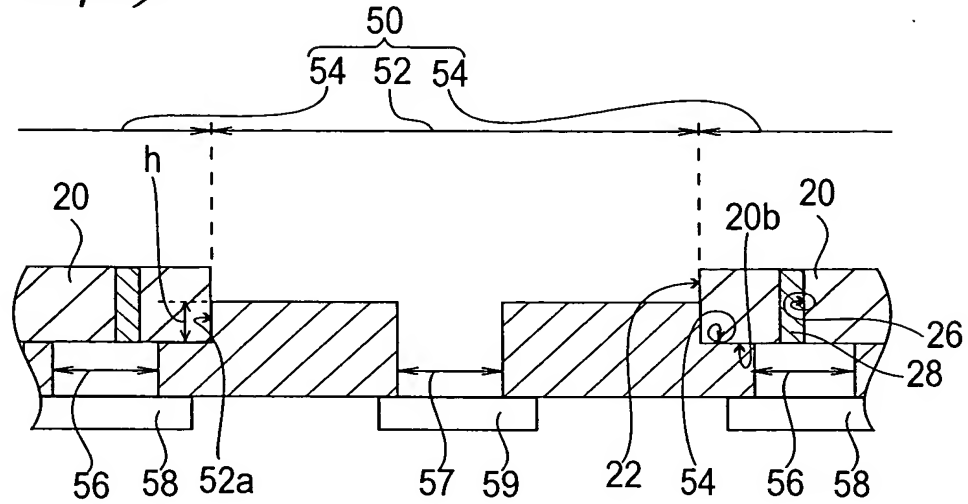
*FIG. 15(A)*



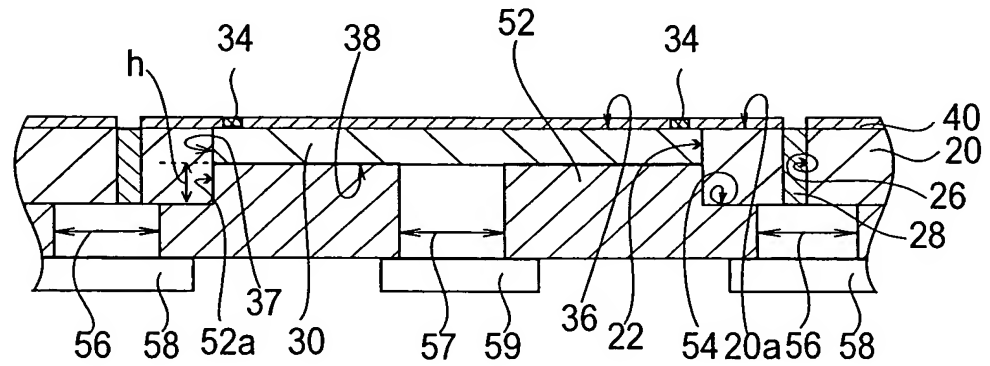
*FIG. 15(B)*



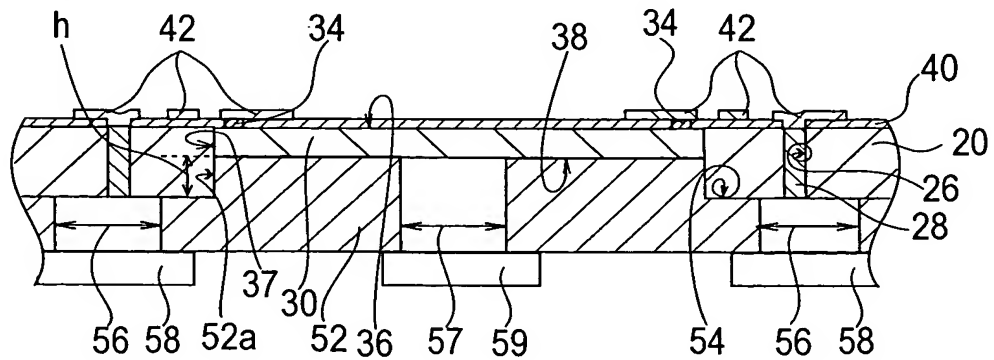
*FIG. 16(A)*



*FIG. 16(B)*

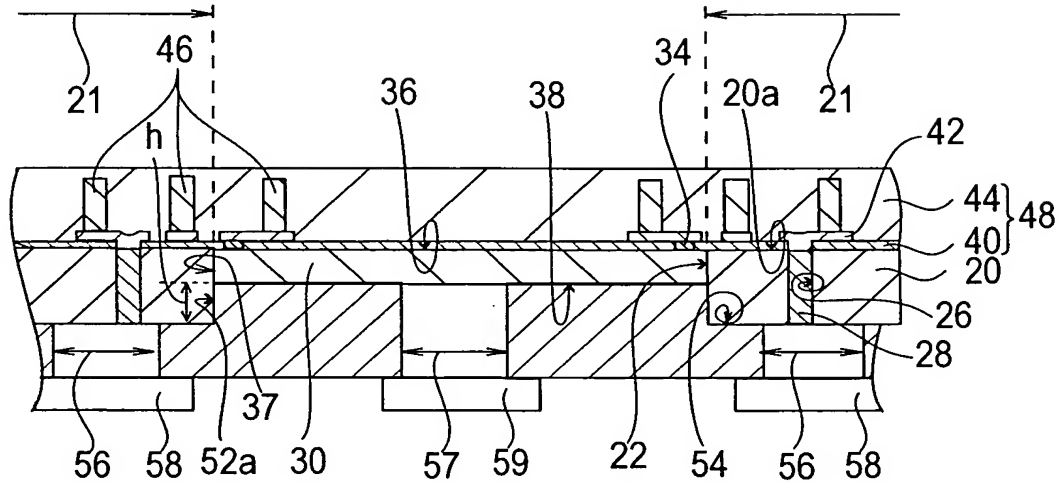


*FIG. 16(C)*

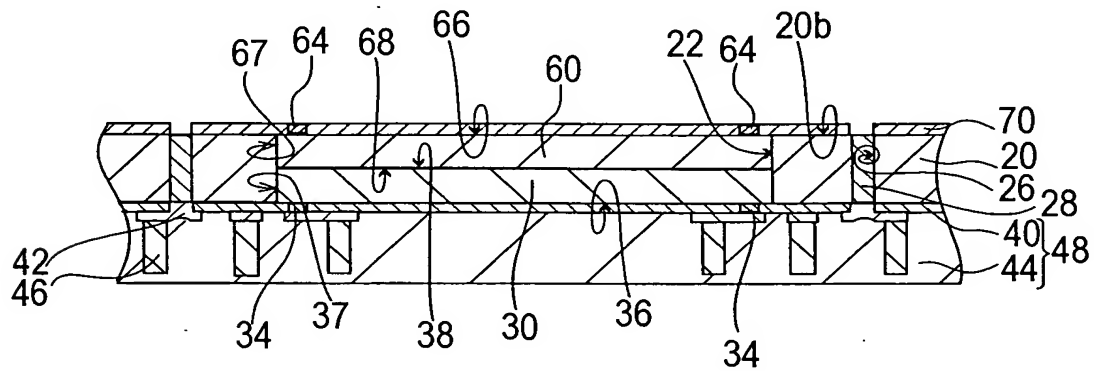




*FIG. 17(A)*



*FIG. 17(B)*



*FIG. 17(C)*

